

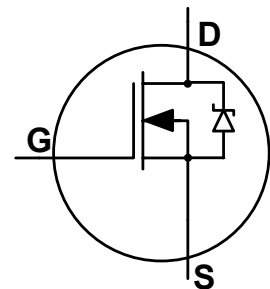
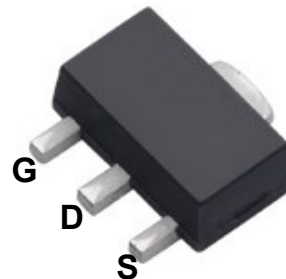
Depletion-Mode Power MOSFET

General Features

- Depletion Mode (Normally On)
- Proprietary Advanced Planar Technology
- Rugged Polysilicon Gate Cell Structure
- Fast Switching Speed
- RoHS Compliant
- Halogen-free available

BV _{DSX}	R _{DS(ON)} (Max.)	I _D
200V	2.0Ω	0.6A

SOT-89



Applications

- Suppressing surge current
- Normally-on Switches
- Converters
- Synchronous Rectification
- Linear Amplifier
- Constant Current Source
- Protection Circuits

Ordering Information

Part Number	Package	Marking	Remark
DMX2023	SOT-89	2023	Halogen Free

Absolute Maximum Ratings

T_A=25°C unless otherwise specified

Symbol	Parameter	DMX2023	Unit
V _{DSX}	Drain-to-Source Voltage ^[1]	200	V
V _{DGX}	Drain-to-Gate Voltage ^[1]	200	V
I _D	Continuous Drain Current	0.6	A
I _{DM}	Pulsed Drain Current ^[2]	2.4	
P _D	Power Dissipation	1.0	W
	Derating Factor above 25°C	0.008	W/°C
V _{GS}	Gate-to-Source Voltage	±20	V
T _L	Soldering Temperature	300	°C
	Distance of 1.6mm from case for 10 seconds		
T _J and T _{STG}	Operating and Storage Temperature Range	-55 to 150	

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

Thermal Characteristics

Symbol	Parameter	DMX2023	Unit
R _{θJC}	Thermal Resistance, Junction-to-Case	125	K/W

Electrical Characteristics

OFF Characteristics

 $T_A = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
BV_{DSX}	Drain-to-Source Breakdown Voltage	200	--	--	V	$V_{GS} = -5V, I_D = 250\mu A$
$I_{D(OFF)}$	Drain-to-Source Leakage Current	--	--	1	μA	$V_{DS} = 200V, V_{GS} = -5V$
		--	--	1	mA	$V_{DS} = 200V, V_{GS} = -5V$ $T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Leakage Current	--	--	1	μA	$V_{GS} = +20V, V_{DS} = 0V$
		--	--	-1		$V_{GS} = -20V, V_{DS} = 0V$

ON Characteristics

 $T_A = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
I_{DSS}	Saturated Drain-to-Source Current	0.6	--	--	A	$V_{GS} = 0V, V_{DS} = 25V$ [3]
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	--	1.3	2.0	Ω	$V_{GS} = 0V, I_D = 0.3A$ [3]
		--	1.1	1.8	Ω	$V_{GS} = 5V, I_D = 0.3A$ [3]
$V_{GS(OFF)}$	Gate-to-Source Cut-off Voltage	-4.0	--	-2.0	V	$V_{DS} = 3V, I_D = 8\mu A$
gfs	Forward Transconductance	--	--	--	S	$V_{DS} = 20V, I_D = 0.3A$

Dynamic Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
C_{ISS}	Input Capacitance	--	--	--	pF	$V_{GS} = -5V$ $V_{DS} = 25V$ $f = 1.0MHz$
C_{OSS}	Output Capacitance	--	--	--		
C_{RSS}	Reverse Transfer Capacitance	--	--	--		
Q_G	Total Gate Charge	--	--	--	nC	$V_{GS} = -5V \sim 5V$ $V_{DS} = 100V, I_D = 0.3A$
Q_{GS}	Gate-to-Source Charge	--	--	--		
Q_{GD}	Gate-to-Drain (Miller) Charge	--	--	--		

Resistive Switching Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$t_{d(ON)}$	Turn-on Delay Time	--	--	--	ns	$V_{GS} = -5V \sim 5V$ $V_{DD} = 100V, I_D = 0.3A$ $R_G = 20\Omega$
t_{rise}	Rise Time	--	--	--		
$t_{d(OFF)}$	Turn-off Delay Time	--	--	--		
t_{fall}	Fall Time	--	--	--		

Source-Drain Diode CharacteristicsT_A=25°C unless otherwise specified

Symbol	Parameter	Min	Typ.	Max.	Units	Test Conditions
V _{SD}	Diode Forward Voltage	--	--	1.5	V	I _{SD} = 0.3 A, V _{GS} = -10 V

NOTE:

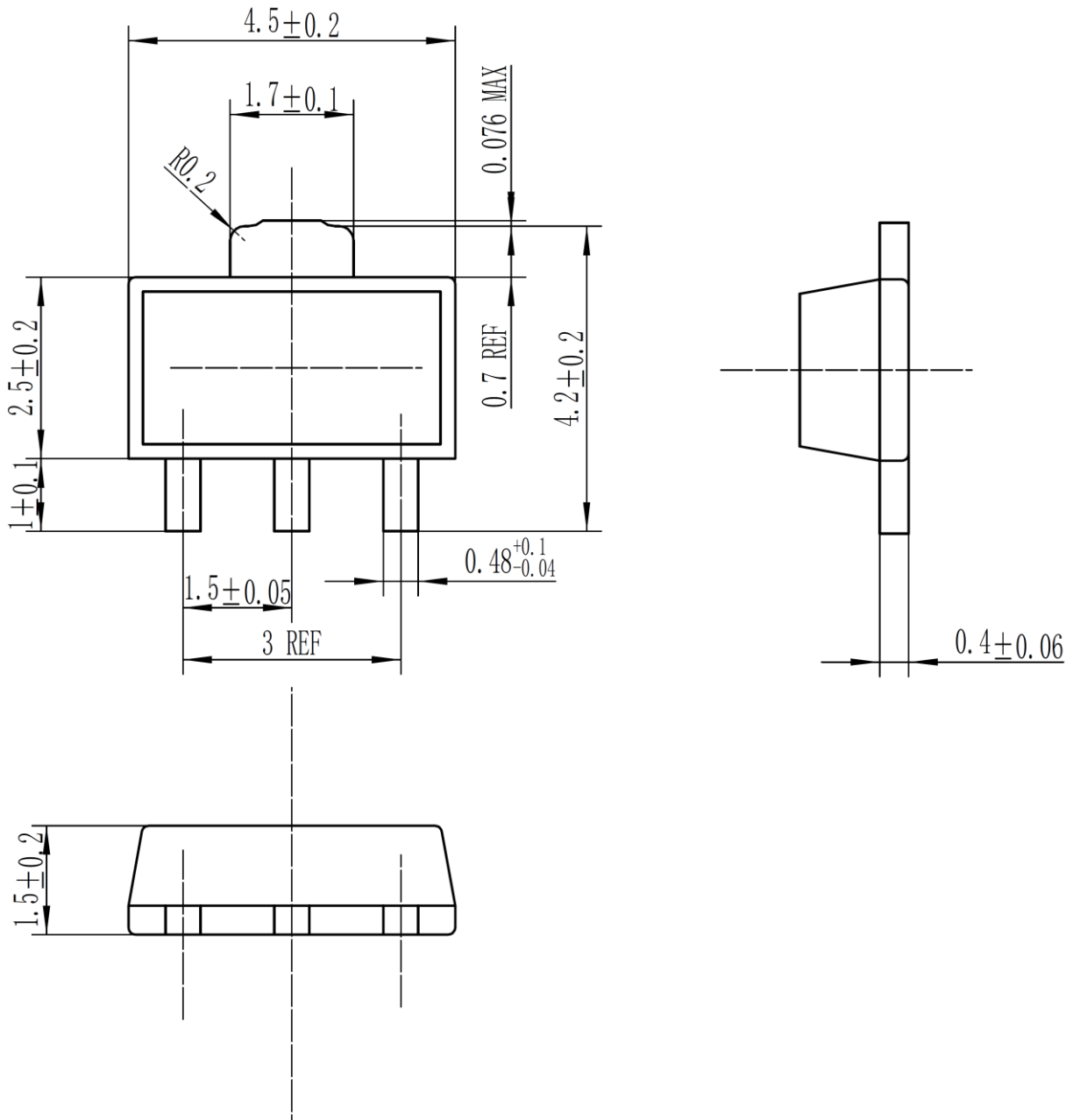
[1] T_J=+25°C to +150°C

[2] Repetitive rating, pulse width limited by maximum junction temperature.

[3] Pulse width ≤ 380 μs; duty cycle ≤ 2%.

Package Dimensions

SOT-89



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